

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-16. (Canceled)

17. (Currently amended): ~~A semiconductor device as claimed in claim 16~~ A semiconductor device having a semiconductor chip,
first electrodes formed on said semiconductor chip,
barrier metals formed on said first electrodes and having laminated structures, and
a plurality of second protruded electrodes, which serve as external connection terminals,
formed on said barrier metals, wherein said barrier metals comprising:
a lowermost conductive metal layer laminated on said first electrodes, said
lowermost conductive metal layer being made of a metal selected from the group consisting of
titanium (Ti), chromium (Cr) and molybdenum (Mo) and having a joining property with said first
electrodes;
an intermediate conductive metal layer laminated on said lowermost conductive
metal layer, said intermediate conductive metal layer being made of nickel (Ni); and
an uppermost conductive metal layer laminated on said one or more intermediate
conductive metal layer, said uppermost conductive metal layer being made of a material which
easily alloys with the nickel of said intermediate conductive metal layer and which has resistance
to oxidation, said uppermost conductive metal layer being made of a metal selected from the group

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consisting of platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or of an alloy containing a metal selected from the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh),

wherein a weight of said uppermost conductive metal layer is less than 2 weight % of a weight of the second protruded electrode formed thereon.